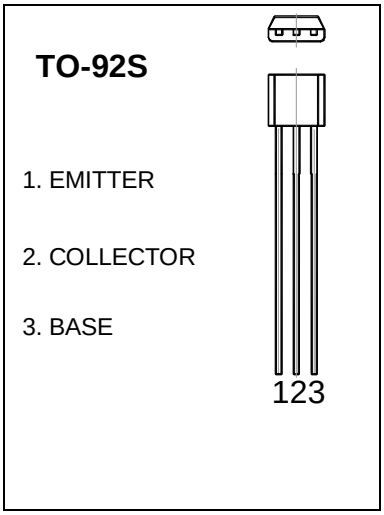
Transys Electronics LIMITED

TO-92S Plastic-Encapsulated Transistors

2SA608S TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 300 mW (Tamb=25℃)

Collector current

I_{CM} : -100 mA

Collector-base voltage

$V_{(BR)CBO}$: -40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA, I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-1mA, I_B=0	-30			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-25V, I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0			-1	μA
DC current gain	h_{FE}	V_{CE}=-6V, I_C=-1mA	60		560	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-50mA, I_B=-5mA			-0.5	V
Transition frequency	f_T	V_{CE}=-6V, I_C=-10mA		180		MHz
Collector output capacitance	Cob	V_{CB}=-6V, f=1MHz		7		pF

CLASSIFICATION OF h_{FE}

Rank	D	E	F	G
Range	60-120	100-200	160-320	280-560